

Oral Session

Keynote/Invited	Presentation NO	Presentation date	Time to start	Time to finish	Account: First name	Account: Middle name	Account: FAMILY NAME	Account: Affiliation	Abstract title
Chairpersons:Dr. Toshihiko Kanayama (AIST, Japan)									
Invited	B-1-I27-001	27 Sep.	13:30	13:50	Roy	G.	GORDON	Harvard University	Vapor Deposition of Materials for Semiconductors
	B-1-O27-002	27 Sep.	13:50	14:05	Kohei		SHIMA	student	High Density Nucleation to Realize Ultra Thin and Continuous CVD-Cu Film Using Ruthenium Glue Layer Applied to Highly Reliable ULSIs
	B-1-O27-003	27 Sep.	14:05	14:20	Brett	Cameron	Johnson	Japan Atomic Energy Agency	Dopant activation by solid phase epitaxy in silicon and germanium
	B-1-O27-004	27 Sep.	14:20	14:35	Daniel		MORARU	Shizuoka University	Experimental and ab initio Study of Donor State Deepening in Nanoscale SOI-MOSFETs
	B-1-O27-005	27 Sep.	14:35	14:50	Koya		HOZAKI	Nagoya University	In situ Sb doping in Ge1-xSnx Epitaxial Layers with High Sn Contents
Coffee Break 27 Sep. 14:50 15:15									
Chairpersons:Prof. Shigeaki Zaima (Nagoya Univ., Japan)									
Invited	B-1-I27-006	27 Sep.	15:15	15:35	Kuan-Neng		CHEN	National Chiao Tung University	Material Analyses and Morphology Investigations of Cu-Based Bonding Technology for 3D Integration
	B-1-O27-007	27 Sep.	15:35	15:50	Vladimir		POBORCHII	National Institute of Advanced Industrial Science and Technology	Enhancement of the Strained Si Doublet Phonon Raman Signal Using Radial Polarization of Light and High Numerical Aperture Lens
	B-1-O27-008	27 Sep.	15:50	16:05	Leonid		BOLOTOV	University of Tsukuba	Built-in Potential Mapping of Silicon Field Effect Transistor Cross Sections by Multimode Scanning Probe Microscopy
	B-1-O27-009	27 Sep.	16:05	16:20	Naoki		TSUNEKAWA	Nagoya University	Temporal Changes of Charge Distribution in High Density Self-aligned Si-based Quantum Dots as Evaluated by AFM/KFM
Coffee Break 27 Sep. 16:20 16:30									
Chairpersons:Prof. Masaaki Niwa (Univ. of Tsukuba, Japan)									
Invited	B-1-I27-010	27 Sep.	16:30	16:50	Yoshiyuki		YAMASHITA	National Institute for Materials Science and Kyusyu University	ICMRS_invited_Yamashita
	B-1-O27-011	27 Sep.	16:50	17:05	Akio		OHTA	Hiroshima University	XPS Study of Energy Band Alignment between Hf-La Oxides and Si(100)
	B-1-O27-012	27 Sep.	17:05	17:20	Jun		CHEN	National Institute for Materials Science	Observation of Leakage Sites in High-k Gate Stack by Using an Electron-Beam-Induced Current Technique
	B-1-O27-013	27 Sep.	17:20	17:35	Matthieu		PY	Kyoto University, Quantum Science and Engineering Center	Low Energy Full Spectrum Time of Flight-SIMS for accurate depth profiling of advanced dielectric/gate stack materials
Chairpersons:Prof. Yee-Chia Yeo (National Univ. of Singapore, Singapore)									
Invited	B-1-I28-001	28 Sep.	9:00	9:20	Roger		LOO	imec	Epitaxial Growth in advanced SiGe and Ge MOS devices: challenges and solutions
	B-1-O28-002	28 Sep.	9:20	9:35	Mohammad		ANISUZZAMAN	Kyushu University	Formation of Germanium Epitaxial Layer on Insulator Using Nanostructured Rapid-Melting-Grown Template
	B-1-O28-003	28 Sep.	9:35	9:50	Takanori		ASANO	Nagoya Univ.	Epitaxial Growth of Ge1-xSnx Layers on (110)-oriented Si and Ge Substrates
	B-1-O28-004	28 Sep.	9:50	10:05	Ryo		MATSUMURA	Kyushu University	Si Segregation Behavior in Giant SiGe Stripes on Insulator during Rapid-Melting-Growth
	B-1-O28-005	28 Sep.	10:05	10:20	Takayoshi		SHIMURA	Graduate School of Engineering, Osaka University	Rapid Melt Growth of Fully Relaxed SiGe Layers with High Ge Concentration on Silicon-on-Insulator Substrates
Coffee Break 28 Sep. 10:20 10:30									
Chairpersons:Prof. Horng-Chih Lin (National Chiao Tung Univ., Taiwan)									
Invited	B-1-I28-006	28 Sep.	10:30	10:50	Edward Yi		CHANG	National Chiao Tung University,	The Growth of III-V and Ge on Si for High-Speed and Low-Power Logic Device Application (Invited)
Invited	B-1-I28-007	28 Sep.	10:50	11:10	Yee-Chia		YEO	National University of Singapore	New Device Structures and Materials for Nano-CMOS
	B-1-O28-008	28 Sep.	11:10	11:25	Hiroataka		YOSHIOKA	Kyushu University	Suppression of Fermi-level pinning at bcc-metal/Ge(111) interfaces
	B-1-O28-009	28 Sep.	11:25	11:40	Hideki		MURAKAMI	Hiroshima University	Photoemission Study of GeO2/Ge Structure Formed by Thermal Oxidation
	B-1-O28-010	28 Sep.	11:40	11:55	shigehisa		SHIBAYAMA	Nagoya University	Thermal Oxidation Mechanism of Ge through Al2O3 Layer Formed on Ge Substrate
	B-1-O28-011	28 Sep.	11:55	12:10	Keisuke		CHIKARAISHI	Graduate School of Engineering, Osaka university	Effective Work Function Control of MIPS/high-k Gate Stacks by Al-incorporation and in situ Low-pressure Oxidation of TiN Surface
	B-1-O28-012	28 Sep.	12:10	12:25	Kuniyuki		KAKUSHIMA	Tokyo Institute of Technology	Interface Controlled Stacked Ni silicidation Process with Schottky Barrier Height Controllability
Lunch 28 Sep. 12:25 13:30									
Chairpersons:Prof. Shigeaki Zaima (Nagoya Univ., Japan)									
Invited	B-1-I28-013	28 Sep.	13:30	13:50	Won-Young		JUNG	Dongbu HiTek	Novel Measurement Method without Self Heating Effect in LD MOS
	B-1-O28-014	28 Sep.	13:50	14:05	Noriyuki		TAOKA	Nagoya University	Importance of Si Bandbending at Zero Bias Condition for Schottky Barrier Height Control at Metal/Si Interfaces with Ultra-thin Al2O3 Layer
	B-1-O28-015	28 Sep.	14:05	14:20	Kenji		OHMORI	University of Tsukuba	Characterization of High-Frequency Noise in MOSFETs
	B-1-O28-016	28 Sep.	14:20	14:35	Horng-Chih		LIN	National Chiao Tung University	Using Si Nanocrystal-Embedded Gate Nitride to Improve Endurance Characteristics of Devices with Suspended Poly-Si Nanowire Channels
	B-1-O28-017	28 Sep.	14:35	14:50	Tzu-I		TSAI	National Chiao Tung University	Low-Operating-Voltage Poly-Si Thin-Film Transistor Technology for RF Applications
	B-1-O28-018	28 Sep.	14:50	15:05	Ko-Hui		LEE	National Chiao Tung University	A Simple Method for Fabricating Sublithographic Short-Channel Tri-Gated Nanowire Poly-Si TFTs
	B-1-O28-019	28 Sep.	15:05	15:20	Shunsuke		ASABA	Graduate School of Engineering, Nagoya University	Electrical Properties of Epitaxially Grown p+-Ge1-xSnx/n-Ge Diodes

Poster Session

Presentation NO	Presentation date	Time to start	Time to finish	Account: First name	Account: Middle name	Account: FAMILY NAME	Account: Affiliation	Abstract title
B-1-P26-001	26 Sep.	16:30	18:30	Young	Kyun	LEE	Pusan National University	Effects of Ceria Oxide-Mixed Abrasive Slurry on the Tetra-Ethyl Ortho-Silicate Oxide Chemical Mechanical Polishing for Planarization of Inter-Layer Dielectric film in the Multilevel Interconnection
B-1-P26-002	26 Sep.	16:30	18:30	Xiao	na	LI	Dalian University of Technology	High performance Cu(NiNb) films for Barrierless Metallization
B-1-P26-003	26 Sep.	16:30	18:30	Leonid		BOLOTOV	University of Tsukuba	Nanoscale characterization of silicon-on-insulator nanowires by multimode scanning probe microscopy
B-1-P26-004	26 Sep.	16:30	18:30	Vladimir		POBORCHII	National Institute of Advanced Industrial Science and Technology	UV Absorption and Raman Enhancement in a Few Nanometer Thick Si-on-Insulator
B-1-P26-005	26 Sep.	16:30	18:30	sungjin		PARK	National Institute of Advanced Industrial Science and Technology (A	Carrier density depth profiling at shallow surface of phosphorus doped crystalline silicon using High Resolution Electron Energy Loss Spectroscopy (HREELS)
B-1-P26-006	26 Sep.	16:30	18:30	Yuji		IKEDA	Kyoto University	Analysis of Local Electric Conductivities for Si Nanowire Models
B-1-P26-007	26 Sep.	16:30	18:30	Nobuya		MORI	Osaka University	Disorder-Induced Enhancement of Impact Ionization Rate in Silicon Nanodots
B-1-P26-008	26 Sep.	16:30	18:30	Masato		SENAMI	Kyoto University	Local Quantity Analysis of Nanosize Electronics and spintronics Material
B-1-P26-009	26 Sep.	16:30	18:30	Ming-Ho		LIN	National Tsing Hua University	Improvement of electrical properties via cyclic and surface D2O plasma treatments on HfO2/La2O3/Ge MOS devices in atomic layer deposition process
B-1-P26-010	26 Sep.	16:30	18:30	Pi-Chun		JUAN	Ming Chi University of Technology	The Effects of Post-Deposition and Post-Metallization Annealing on the Physical and Electrical Properties of Metal-Gate (ZrN)/High-k Dielectric (LaZrO)/Si MIS Structures
B-1-P26-011	26 Sep.	16:30	18:30	Katsumasa		KAMIYA	University of Tsukuba	Work Functions of Curved Aluminum Surfaces
B-1-P26-012	26 Sep.	16:30	18:30	Ryo		MATSUMURA	Kyushu University	Formation of N-Type Ge-on-Insulator through P-Implantation and Rapid-Melting Growth
B-1-P26-013	26 Sep.	16:30	18:30	Yu-Ting		LIN	National Central University	Thermal stability of supersaturated carbon incorporation in silicon
B-1-P26-014	26 Sep.	16:30	18:30	Amal		CHABLI	CEA-Leti	New generation state-of-the-art Auger Nanoprobes for the analysis of Si/SiGe superlattice heterostructures